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N-Channel MOSFET Transistor

IRF634

DESCRIPTION

- Drain Current - $I_D=8.1A$ @ $T_C=25^\circ C$
- Drain Source Voltage-
 - : $V_{DSS}= 250V$ (Min)
- Static Drain-Source On-Resistance
 - : $R_{DS(on)} = 0.45 \Omega$ (Max)
- Fast Switching Speed
- Low Drive Requirement

APPLICATIONS

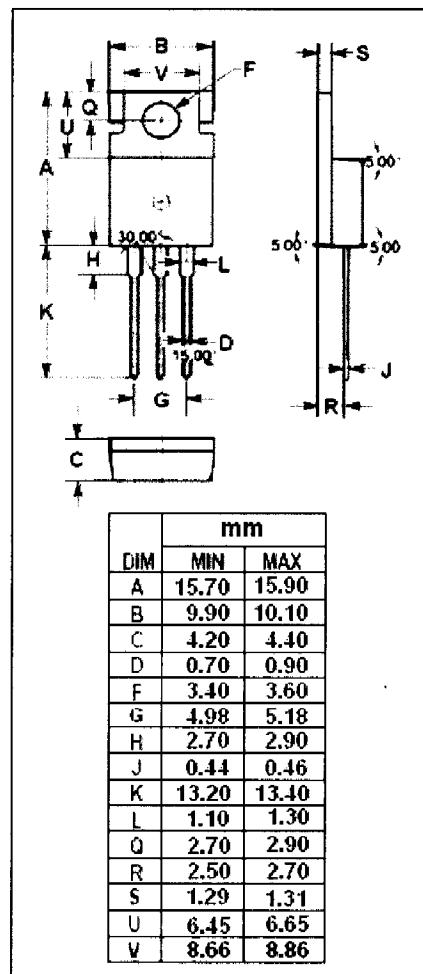
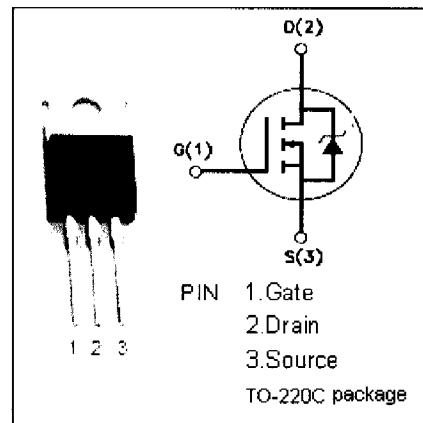
- High current , high speed switching
- Switch mode power supplies
- DC-DC converters for telecom, industrial, and lighting equipment ideal for monitor's B+ function

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

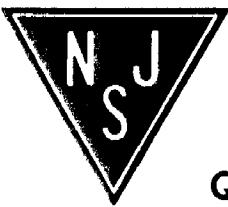
SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	250	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $TC=25^\circ C$	8.1	A
P_{tot}	Total Dissipation@ $TC=25^\circ C$	74	W
T_J	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	1.56	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	62.5	$^\circ C/W$



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N-Channel Mosfet Transistor

IRF634

ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0$; $I_D=0.25\text{mA}$	250		V
$V_{\text{GS}(\text{TH})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$; $I_D=0.25\text{mA}$	2	4	V
$R_{\text{DS}(\text{ON})}$	Drain-Source On-stage Resistance	$V_{\text{GS}}=10\text{V}$; $I_D=5.1\text{A}$		0.45	Ω
I_{GSS}	Gate Source Leakage Current	$V_{\text{GS}}= \pm 20\text{V}$; $V_{\text{DS}}=0$		± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=250\text{V}$; $V_{\text{GS}}=0$		25	μA
V_{SD}	Diode Forward Voltage	$I_F=8.1\text{A}$; $V_{\text{GS}}=0$		2.0	V